

R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	6.4718	N/A	11.8772
RT2	20.2604	N/A	5.2866
RT3	30.5059	N/A	9.7413
RT4	52.7619	N/A	11.0949
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	171.9710 u	N/A	9.3312 m
CT2	58.6522 m	N/A	77.1336 u
CT3	2.8148 m	N/A	979.8345 u
CT4	1.6221	N/A	2.6698 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ($^{\circ}\text{C}/\text{W}$)			
Junction to	Ambient	Case	Foot
RF1	9.4286	N/A	7.8883
RF2	30.1231	N/A	8.9091
RF3	19.0764	N/A	11.9601
RF4	51.3719	N/A	9.2425
Thermal Capacitance (Joules/ $^{\circ}\text{C}$)			
Junction to	Ambient	Case	Foot
CF1	236.6841 u	N/A	88.4265 u
CF2	2.9295 m	N/A	860.3847 u
CF3	54.3607 m	N/A	15.7396 u
CF4	1.5915	N/A	9.6868 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya, IEEE / SEMITHERM 2002

